



A Product Line of Diodes Incorporated

DMN2300UFB

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> max T <sub>A</sub> = +25°C	
	175mΩ @ V <sub>GS</sub> = 4.5V	1.30A	
20V	240mΩ @ V <sub>GS</sub> = 2.5V	1.11A	
	360mΩ @ V <sub>GS</sub> = 1.8V	0.91A	

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

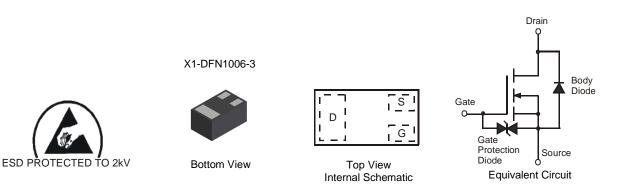
### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features and Benefits**

- Footprint of just 0.6mm<sup>2</sup> thirteen times smaller than SOT23
- 0.5mm profile ideal for low profile applications
- On resistance <200m $\Omega$  @ V<sub>GS</sub> = 4.5V
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate 2KV
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.001 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2300UFB-7	NI	7	8	3,000
DMN2300UFB-7B	NI	7	8	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

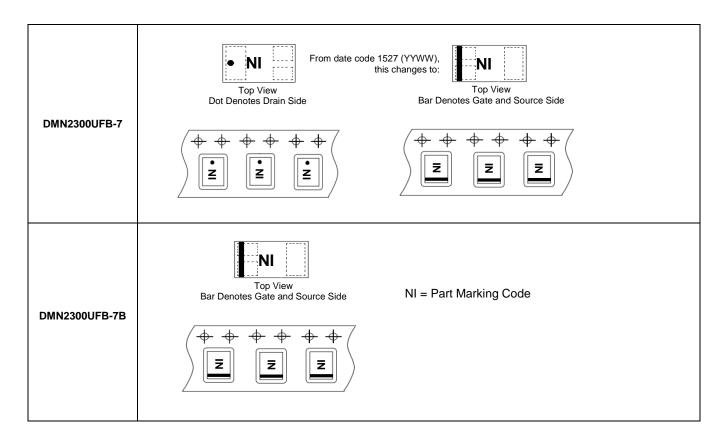
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**





# DMN2300UFB

## **Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current	Steady State	$T_A = +25^{\circ}C$ (Note 5) $T_A = +85^{\circ}C$ (Note 5) $T_A = +25^{\circ}C$ (Note 6)	ID	1.32 0.94 1.78	A
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	8	А	

#### Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.468	W
Power Dissipation (Note 6)	PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	267	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	104	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symphol	Min	Tum	Max	Unit	Test Condition	
	Symbol	WIIN	Тур	wax	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			1				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	-	-	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	10	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45	-	0.95	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
		-	-	175		$V_{GS} = 4.5V, I_D = 300mA$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	-	-	240	mΩ	$V_{GS} = 2.5V, I_D = 250mA$	
	- ( - /	-	-	360		$V_{GS} = 1.8V, I_D = 100mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	40	-	-	mS	$V_{DS} = 3V, I_D = 30mA$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS						*	
Input Capacitance	Ciss	-	67.62	-	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	C <sub>oss</sub>	-	9.74	-	pF		
Reverse Transfer Capacitance	Crss	-	7.58	-	pF	1 = 1.000112	
Gate Resistance	Rg	-	68.51	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	-	0.89	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	0.14	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.16	-	nC	$I_D = 1A$	
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.92	-	ns		
Turn-On Rise Time	tr	-	6.93	-	ns	$V_{DS} = 10V, I_{D} = 1A$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	21.71	-	ns	$V_{GS} = 4.5V, R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	-	10.62	-	ns		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm X 25mm square copper plate.

7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

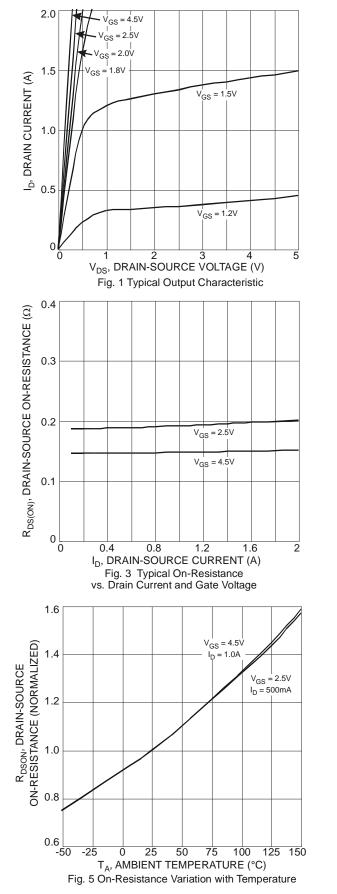
8. Short duration pulse test used to minimize self-heating effect.

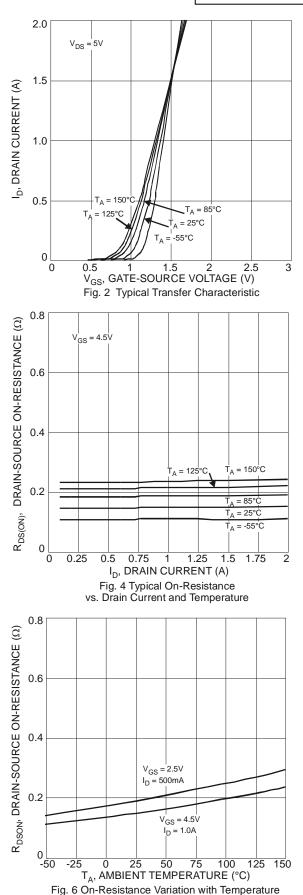


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**ZETEX** 



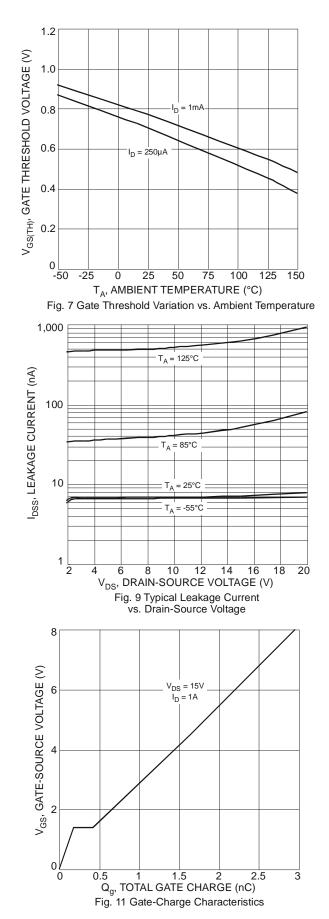


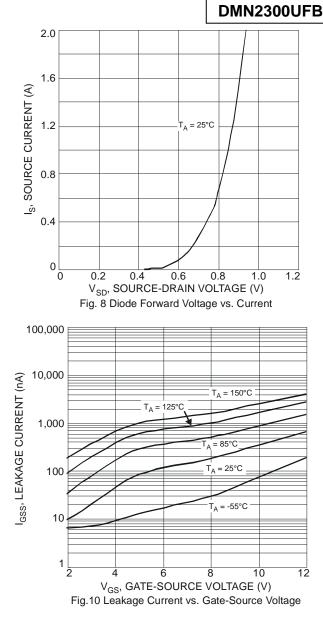
DMN2300UFB Document number: DS35235 Rev. 2 - 2 4 of 8 www.diodes.com



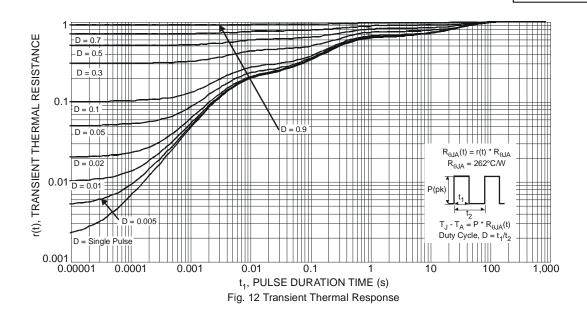
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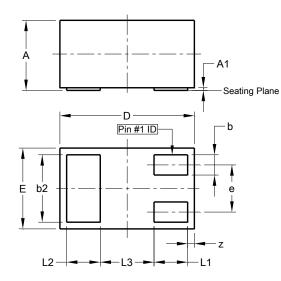




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## **Package Outline Dimensions**

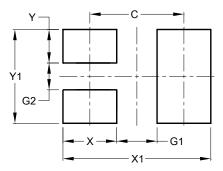
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Х	X1-DFN1006-3					
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
Е	0.55	0.675	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
z	0.02	0.08	0.05			
All D	All Dimensions in mm					

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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